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(54) Title: ANODE BATTERY MATERIALS AND METHODS OF MAKING THE SAME

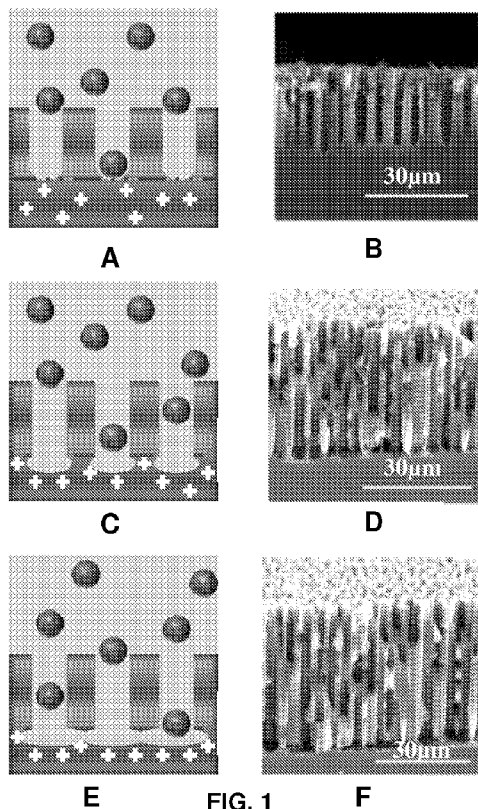


FIG. 1

(57) Abstract: In some embodiments, the present invention provides novel methods of preparing porous silicon films and particles for lithium ion batteries. In some embodiments, such methods generally include: (1) etching a silicon material by exposure of the silicon material to a constant current density in a solution (e.g., hydrofluoric acid solution) to produce a porous silicon film over a substrate; and (2) separating the porous silicon film from the substrate by gradually increasing the electric current density in sequential increments. In some embodiments, the methods of the present invention may also include a step of associating the porous silicon film with a binding material, such as polyacrylonitrile (PAN). In some embodiments, the methods of the present invention may also include a step of splitting the porous silicon film to form porous silicon particles.



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